IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

NAKAYAMA ET AL.

Atty. Ref.:

925-342

Serial No.

10/581,247

2811 Group:

Filed:

May 31, 2006

Examiner: Unknown

For:

SILICON CARBIDE SEMICONDUCTOR DEVICE AND

MANUFACTURING METHOD THEREFOR

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

☐ All listed documents are attached.

Copies of U.S. Patent Publications are not required and are not attached.

□ Listed foreign patent publications and other documents are enclosed.

The EP 1215730 reference corresponds to the WO 01/018872 reference; U.S.

Patent 6,121,633 corresponds to the JP 2002-514355 reference; and U.S. Patent 5,958,132 corresponds to the JP 7-267795 reference..

The listed documents were cited in the ISR and copies are submitted herewith for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

NAKAYAMA ET AL. Serial No. 10/581,247

> The Commissioner is authorized to charge the undersigned's deposit account #14-1140 in whatever amount is necessary for entry of these papers and the continued pendency of the captioned application.

> > Respectfully submitted,
> > NIXON & VANDERHYE P.C.

By: Haller Seese

Reg. No. 29,366

January 8, 2007

HWB:lsh 901 North Glebe Road, 11th Floor Arlington, VA 22203-1808 Telephone: (703) 816-4000 Facsimile: (703) 816-4100

- 2 -

INFOR	MATION DISCLOSURE	ATTY. I	OCKET NO.	SE	RIAL NO.			
CITATION		925-342			10/581,247			
	6.5		AYAMA ET AL					
(Use	soverersheets if necessary	FILING			ROUP			
	(JAN 0 8 2007 &	May	31, 2006	2	811			
	البقا	Ţ	S. PATENT DOCU	MENTS				
XAMINER INITIAL	GCUMENT NUMBER	DATE	N/	AME	CLASS	SUBCLASS	FILING IF APPRO	
r.G./	5.958 132	9-1999		shi et al.				
8	6,121,633	9-2000	Singl	h et al.				
1								
1								
1	1							
+ +								
_								
+								
+		FC	REIGN PATENT D	OCUMENTS				
1							TRANS	LATIO
1	DOCUMENT	DATE	cou	INTRY	CLASS	SUBCLASS	YES	NC
\top	2001/018872 A1	3-2001	V	VO			Х	
1-	2000-001398 A	1-2000		JP			Partial	
1	03-171772 A	7-1999		JP			Partial	
+	2002-514355 A	5-2002		JP			Partial	
1	11-060390 A	3-1999		JP .			Partial	
1-	7-267795 A	10-1995		JP			Partial	
1	1 215 730 A1	6-2002	Е	EP				
1		-						
1	OTHER DOO	UMENTS (including Author,	Title, Date, Pertir	nent pages,	etc.)		
	Translation of the Inte	rnational Pr	eliminary Report on				rrespon	ding
	PCT application no. P	CT/JP2004	017888					
	Matsunami, "Semiconductor SiC Technology and Applications", Nikkan Kogyo Shimbunsha, pp. 218-221 (2							
	Agarwal et al, "Dynamic Performance of 3.1 kV 4H-SiC Asymmetrical GTO Thyristors", Materials Science							
\mathbb{I}	Forum Vols. 389-393, (2002), pp. 1349-1352 Lendenmann et al, "High-Power SiC Diodes: Characteristics, Reliability and Relation to Material Defects",							
	Materials Science Forum Vols, 389-393, (2002), pp. 1259-1264							
J	Matsunami et al., "Ste	p-Controlle	Epitaxial Growth of	of SiC: High Qual	ity Homoepit	axy", Materi	als Scie	nce a
w	Engineering, R20, Re	ports: A Re	riew Journal, (1997)), pp. 125-166				
xaminer	/Telly Green/ Date Considered 03/16/2010							